

DEFECT-GOVERNED LOW-TEMPERATURE REDOX TRANSFORMATIONS IN Ar⁺-IRRADIATED TiO₂ SURFACES

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In this presentation, we report on the modification of rutile TiO₂ surfaces induced by low-energy Ar⁺ ion irradiation. The TiO₂ surfaces were irradiated with 2 keV Ar⁺ ions at moderate fluences of up to 10¹⁷ ions/cm². The resulting structural and electronic changes were investigated using local-conductivity atomic force microscopy, in situ electron diffraction techniques, including μ LEED/LEEM, and X-ray photoelectron spectroscopy. The results show that ion irradiation produces a strongly reduced near-surface region extending over several tens of nanometers, accompanied by pronounced changes in local conductivity and surface ordering.

Particular attention is given to the thermal reoxidation of Ar-sputtered TiO₂(110). Using operando X-ray photoelectron spectroscopy and electron diffraction under UHV conditions, we demonstrate that redox processes in irradiated TiO₂ begin already well below 400 °C, significantly lower than commonly assumed for this material. Reoxidation does not proceed through simple restoration of an ideal stoichiometric lattice, but is instead governed by extended structural defects that are inherently present in real crystals and further activated by ion irradiation. These defects act as highly efficient pathways for oxygen migration, coupling ionic transport with electronic conduction and enabling a global insulator–metal transition under relatively mild annealing conditions.